



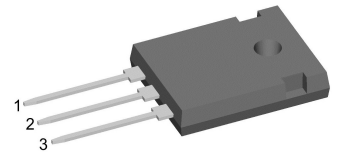
HiPerFRED

$V_{RRM} = 200\text{ V}$
 $I_{FAV} = 2 \times 30\text{ A}$
 $t_{rr} = 55\text{ ns}$

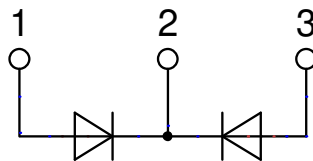
High Performance Fast Recovery Diode
 Low Loss and Soft Recovery
 Common Cathode

Part number

DPF60C200HB



Backside: cathode



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm} -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: TO-247

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

Disclaimer Notice

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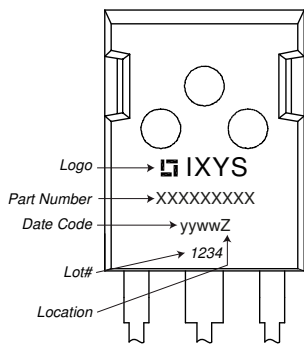


Fast Diode				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			200	V	
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			200	V	
I_R	reverse current, drain current	$V_R = 200 V$	$T_{VJ} = 25^{\circ}C$		5	μA	
		$V_R = 200 V$	$T_{VJ} = 150^{\circ}C$		0.25	mA	
V_F	forward voltage drop	$I_F = 30 A$	$T_{VJ} = 25^{\circ}C$		1.11	V	
		$I_F = 60 A$			1.30	V	
		$I_F = 30 A$	$T_{VJ} = 150^{\circ}C$		0.91	V	
		$I_F = 60 A$			1.11	V	
I_{FAV}	average forward current	$T_C = 150^{\circ}C$ rectangular $d = 0.5$	$T_{VJ} = 175^{\circ}C$		30	A	
V_{FO}	threshold voltage	} for power loss calculation only	$T_{VJ} = 175^{\circ}C$		0.67	V	
r_F	slope resistance				6.6	m Ω	
R_{thJC}	thermal resistance junction to case				0.95	K/W	
R_{thCH}	thermal resistance case to heatsink			0.3		K/W	
P_{tot}	total power dissipation		$T_C = 25^{\circ}C$		160	W	
I_{FSM}	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}; V_R = 0 \text{ V}$	$T_{VJ} = 45^{\circ}C$		400	A	
C_J	junction capacitance	$V_R = 150 \text{ V}$ $f = 1 \text{ MHz}$	$T_{VJ} = 25^{\circ}C$		42	pF	
I_{RM}	max. reverse recovery current	} $I_F = 30 \text{ A}; V_R = 100 \text{ V}$ $-di_F / dt = 200 \text{ A}/\mu\text{s}$	$T_{VJ} = 25^{\circ}C$		6	A	
			$T_{VJ} = 125^{\circ}C$		10	A	
t_{rr}	reverse recovery time		$T_{VJ} = 25^{\circ}C$		55	ns	
			$T_{VJ} = 125^{\circ}C$		85	ns	



Package TO-247			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal ¹⁾			50	A
T_{VJ}	virtual junction temperature		-55		175	°C
T_{op}	operation temperature		-55		150	°C
T_{stg}	storage temperature		-55		150	°C
Weight				6		g
M_D	mounting torque		0.8		1.2	Nm
F_C	mounting force with clip		20		120	N

Product Marking



Part description

- D = Diode
- P = HiPerFRED
- F = ultra fast
- 60 = Current Rating [A]
- C = Common Cathode
- 200 = Reverse Voltage [V]
- HB = TO-247AD (3)

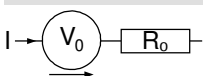
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DPF60C200HB	DPF60C200HB	Tube	30	511115

Similar Part	Package	Voltage class
DPF60C200HJ	ISOPLUS247 (3)	200
DPG60C200HB	TO-247AD (3)	200
DPG60C200QB	TO-3P (3)	200
DPF80C200HB	TO-247AD (3)	200

Equivalent Circuits for Simulation

** on die level*

$T_{VJ} = 175^{\circ}C$



Fast Diode

$V_{0\ max}$	threshold voltage	0.67	V
$R_{0\ max}$	slope resistance *	4	mΩ



Outlines TO-247



Sym.	Inches		Millimeter	
	min.	max.	min.	max.
A	0.185	0.209	4.70	5.30
A1	0.087	0.102	2.21	2.59
A2	0.059	0.098	1.50	2.49
D	0.819	0.845	20.79	21.45
E	0.610	0.640	15.48	16.24
E2	0.170	0.216	4.31	5.48
e	0.215 BSC		5.46 BSC	
L	0.780	0.800	19.80	20.30
L1	-	0.177	-	4.49
Ø P	0.140	0.144	3.55	3.65
Q	0.212		5.38	
S	0.242 BSC		6.14 BSC	
b	0.039	0.055	0.99	1.40
b2	0.065	0.094	1.65	2.39
b4	0.102	0.135	2.59	3.43
c	0.015	0.035	0.38	0.89
D1	0.515	-	13.07	-
D2	0.020	0.053	0.51	1.35
E1	0.530	-	13.45	-
Ø P1	-	0.29	-	7.39



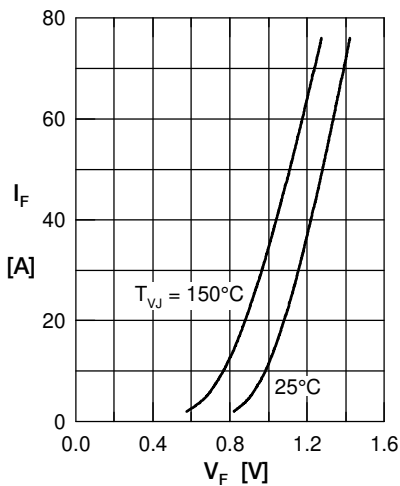
Fast Diode


Fig. 1 Forward current I_F versus V_F

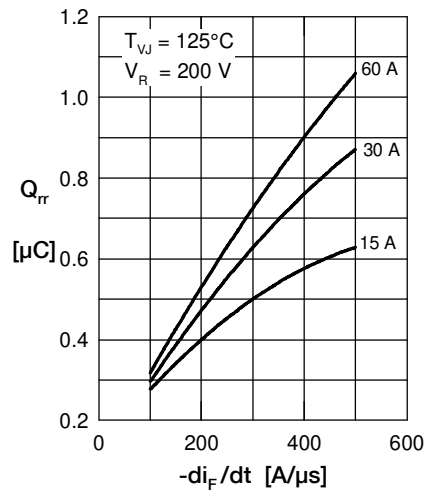


Fig. 2 Typ. reverse recov. charge Q_{rr} versus $-di_F/dt$

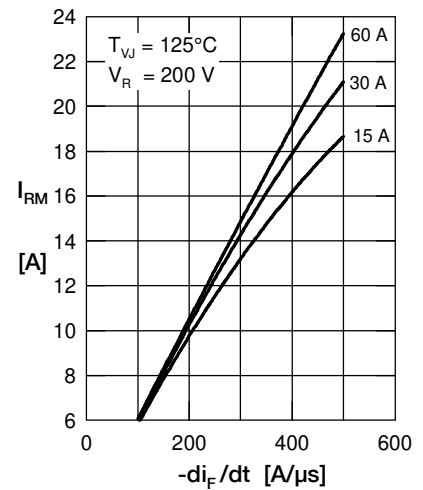


Fig. 3 Typ. reverse recov. current I_{RM} versus $-di_F/dt$

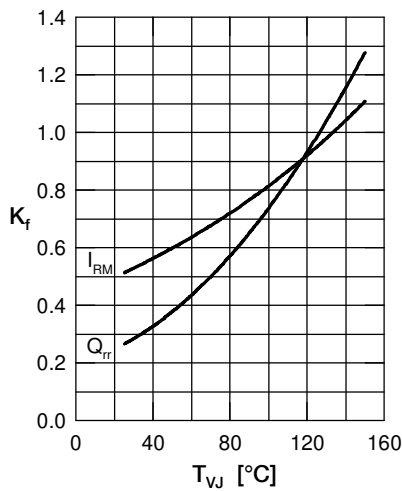


Fig. 4 Typ. dynamic parameters Q_{rr} , I_{RM} versus T_{VJ}

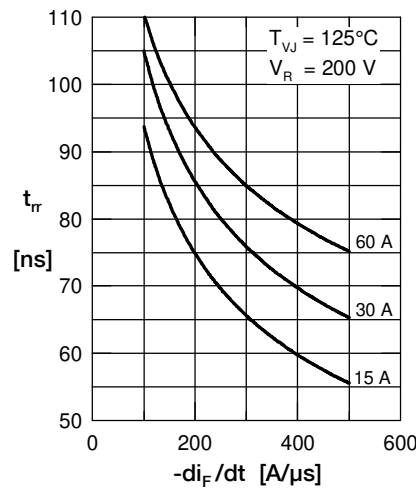


Fig. 5 Typ. reverse recov. time t_{rr} versus $-di_F/dt$

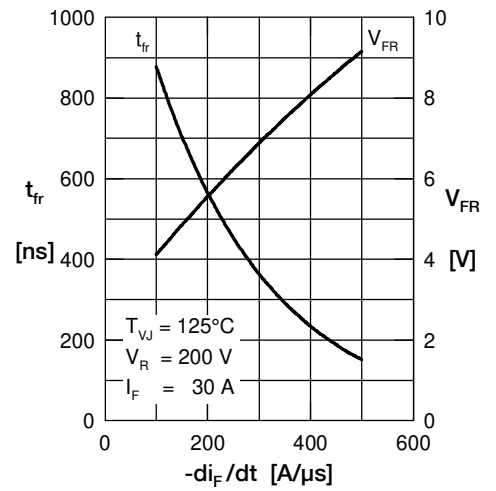


Fig. 6 Typ. forward recovery voltage V_{FR} & time t_{fr} versus di_F/dt

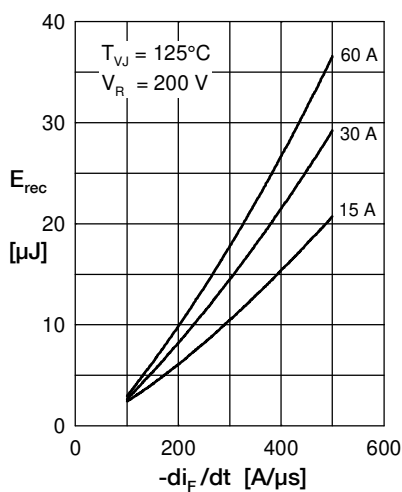


Fig. 7 Typ. recovery energy E_{rec} versus $-di_F/dt$

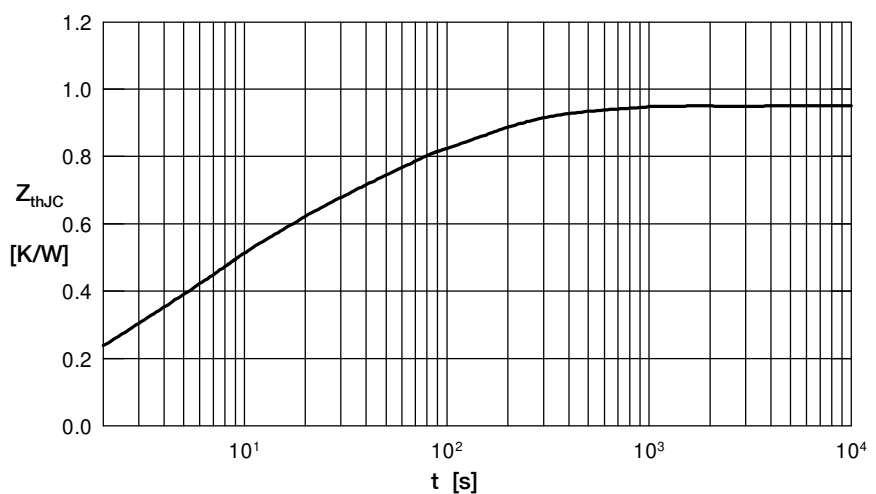


Fig. 8 Transient thermal impedance junction to case